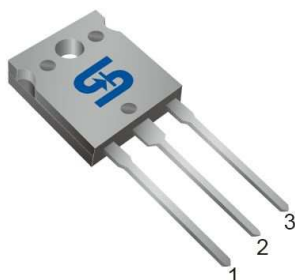


TO-264



Pin Definition:

1. Gate
2. Collector
3. Emitter

PRODUCT SUMMARY

V_{CES} (V)	V_{GES} (V)	I_C (A)
1200	± 20	40

General Description

The TSG40N120CE using proprietary trench design and advanced NPT technology, the 1200V NPT IGBT offers superior conduction and switching performances, high avalanche ruggedness and easy parallel operation. This device is well suited for the resonant or soft switching application such as induction heating, microwave oven, etc.

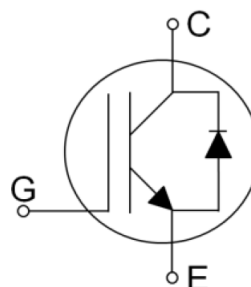
Features

- 1200V NPT Trench Technology
- High Speed Switching
- Low Conduction Loss

Ordering Information

Part No.	Package	Packing
TSG40N120CE C0	TO-264	25pcs / Tube

Block Diagram



NPT Trench IGBT

Absolute Maximum Rating ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Collector-Emitter Voltage		V _{CES}	1200	V
Gate-Emitter Voltage		V _{GES}	±20	V
Continuous Current	T _C =25°C	I _C	64	A
	T _C =100°C		40	A
Pulsed Collector Current *		I _{CM}	120	A
Diode Forward Current (T _C =100°C)		I _F	40	A
Diode Pulse Forward Current		I _{FM}	240	A
Max Power Dissipation	T _J =25°C	P _D	208	W
	T _J =100°C		83	
Operating Junction Temperature		T _J	-55 to +150	°C
Storage Temperature Range		T _{STG}	-55 to +150	°C

* Repetitive rating: Pulse width limited by max. junction temperature

Thermal Performance

Parameter		Symbol	Limit	Unit
Thermal Resistance - Junction to Case	IGBT	$R\theta_{JC}$	0.6	$^{\circ}\text{C/W}$
	DIODE		2.2	
Thermal Resistance - Junction to Ambient		$R\theta_{JA}$	25	

Electrical Specifications (T_c=25 $^{\circ}$ C unless otherwise noted)

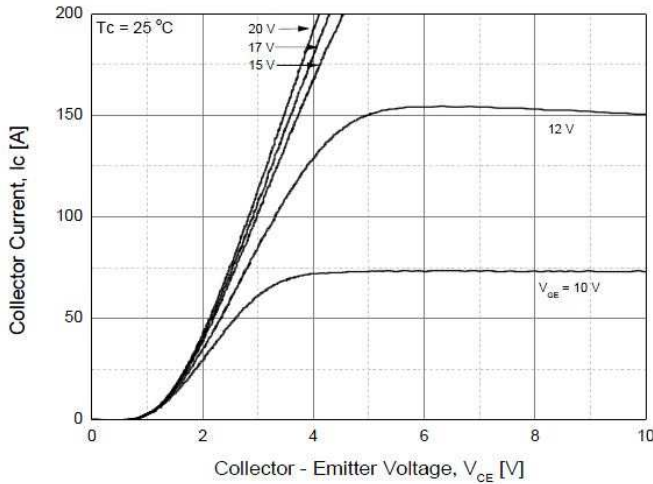
Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Static						
Collector-Emitter Breakdown Voltage	$V_{GE} = 0V, I_C = 1mA$	BV_{CES}	1200	--	--	V
Zero Gate Voltage Collector Current	$V_{CE} = 1200V, V_{GE} = 0V$	I_{CES}	--	--	1	mA
Gate-Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$	I_{GES}	--	--	±250	nA
Gate-Emitter Threshold Voltage	$V_{GE} = V_{CE}, I_C = 40mA$	$V_{GE(TH)}$	4.0	6.0	8.0	V
Collector-Emitter Saturation Voltage	$V_{GE} = 15V, I_C = 40A, T_J = 25^{\circ}C$	$V_{CE(SAT)}$	--	2	2.8	V
	$V_{GE} = 15V, I_C = 40A, T_J = 125^{\circ}C$	$V_{CE(SAT)}$	--	2.5	--	V
Dynamic						
Input Capacitance	$V_{CE} = 30V, V_{GE} = 0V,$ $f = 1.0MHz$	C_{IES}	--	5150	--	pF
Output Capacitance		C_{OES}	--	150	--	
Reverse Transfer Capacitance		C_{RES}	--	100	--	
Switching						
Turn-On Delay Time	$V_{CC} = 600V, I_C = 40A,$ $R_G = 5\Omega, V_{GE} = 15V$ Inductive Load, $T_J = 25^{\circ}C$	$t_{d(on)}$	--	41	--	nS
Rise Time		t_r	--	82	--	
Turn-Off Delay Time		$t_{d(off)}$	--	200	--	
Fall Time		t_f	--	85	170	
Turn-On Switching Loss		E_{on}	--	5.8	8.7	mJ
Turn-Off Switching Loss		E_{off}	--	1.5	2.3	
Total Switching Loss		E_{ts}	--	7.3	11	
Turn-On Delay Time	$V_{CC} = 600V, I_C = 40A,$ $R_G = 5\Omega, V_{GE} = 15V$ Inductive Load, $T_J = 125^{\circ}C$	$t_{d(on)}$	--	45	--	nS
Rise Time		t_r	--	76	--	
Turn-Off Delay Time		$t_{d(off)}$	--	212	--	
Fall Time		t_f	--	189	--	
Turn-On Switching Loss		E_{on}	--	5.6	5	mJ
Turn-Off Switching Loss		E_{off}	--	3.3	5	
Total Switching Loss		E_{ts}	--	8.9	13.4	
Total Gate Charge	$V_{CC} = 600V, I_C = 40A,$ $V_{GE} = 15V$	Q_g	--	210	315	nC
Gate-Emitter Charge		Q_{ge}	--	50	75	
Gate-Collector Charge		Q_{gc}	--	115	173	

Electrical Specifications of the DIODE (Tc=25°C unless otherwise noted)

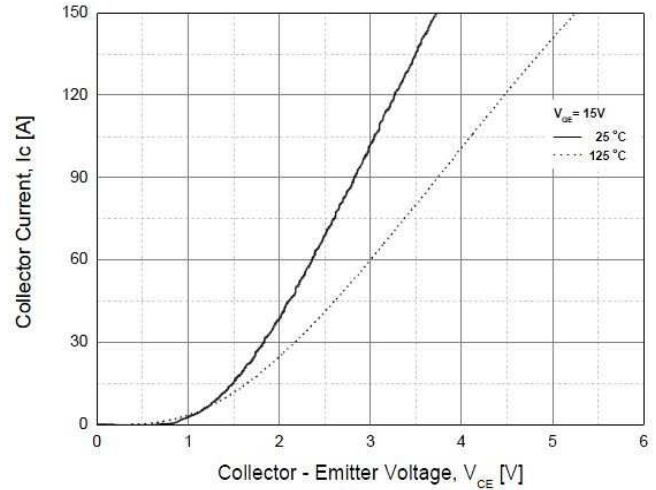
Parameter	Conditions		Symbol	Min	Typ	Max	Unit
Diode Forward Voltage	I _F = 40A,	T _J =25°C	V _{FM}	--	2.8	--	V
		T _J =125°C		--	2.9	--	V
Reverse Recovery Time	I _F = 40A, dI/dt=200A/us	T _J =25°C	t _{fr}	--	220	--	ns
		T _J =125°C		--	3 10	--	
T _J =25°C		I _{fr}	--	24	--	A	
T _J =125°C			--	36	--		
Reverse Recovery Charge		T _J =25°C	Q _{fr}	--	2600	--	nC
		T _J =125°C		--	5580	--	

Electrical Characteristics Curve ($T_c = 25^\circ\text{C}$, unless otherwise noted)

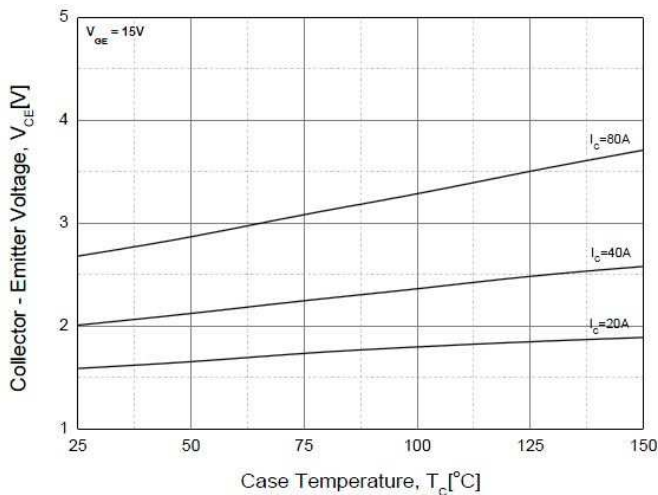
Output Characteristics



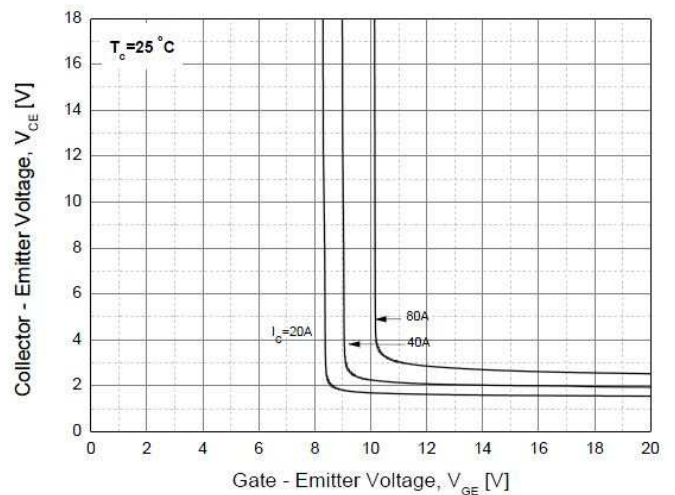
Saturation voltage characteristics



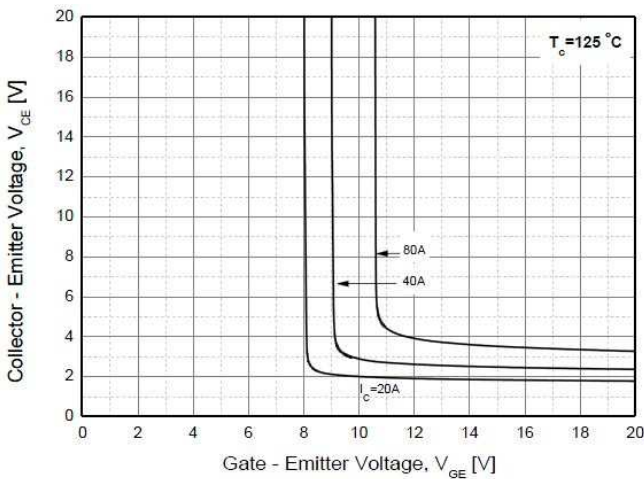
Saturation voltage vs. collector current



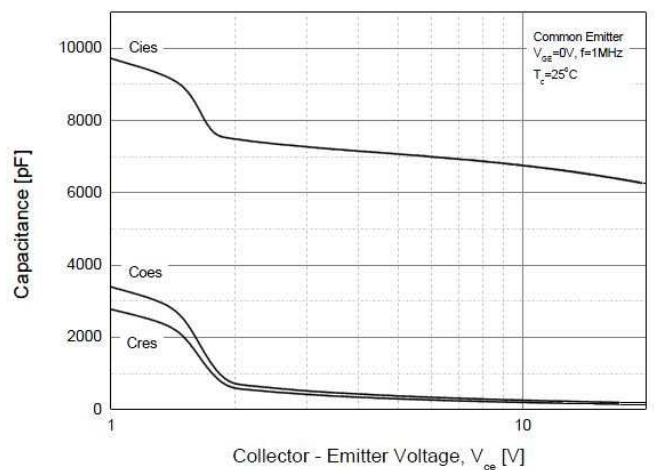
Saturation voltage vs. gate bias



Saturation voltage vs. gate bias

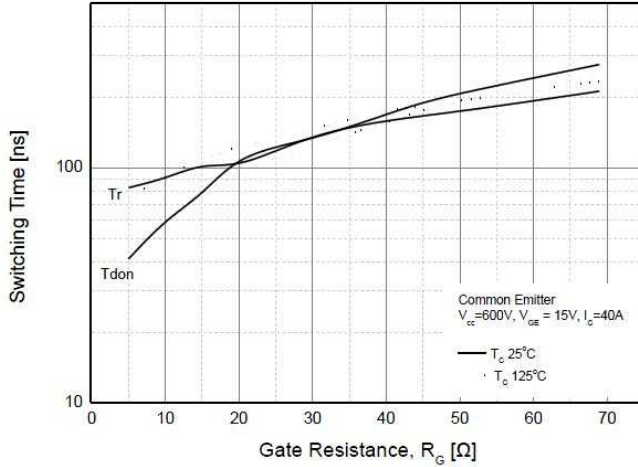


Capacitance characteristics

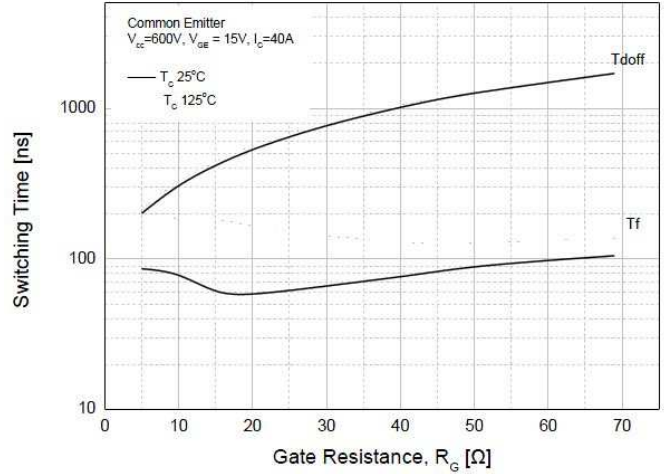


Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

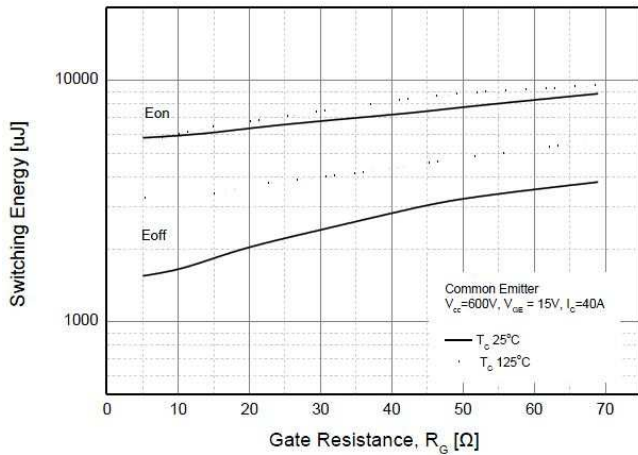
Turn on time vs. gate resistance



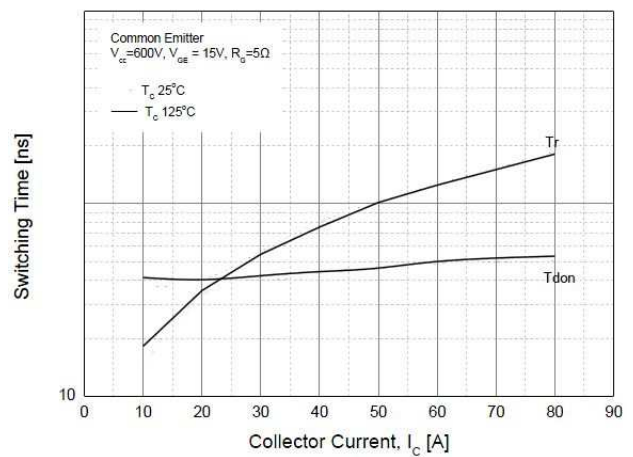
Turn off time vs. gate resistance



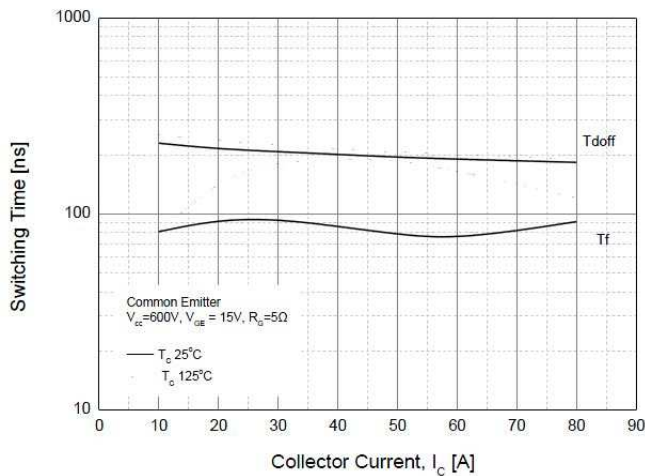
Switching loss vs. gate resistance



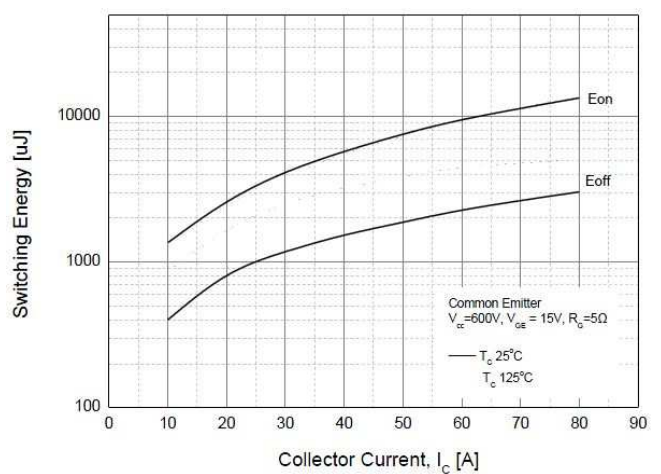
Turn on time vs. collector current



Turn off time vs. collector current

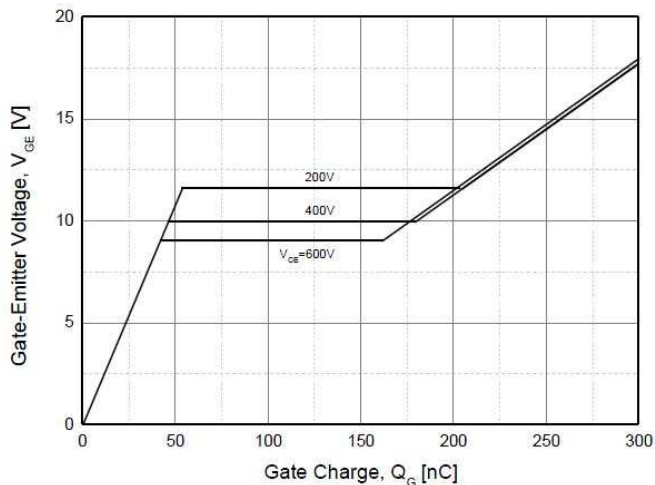


Switching loss vs. collector current

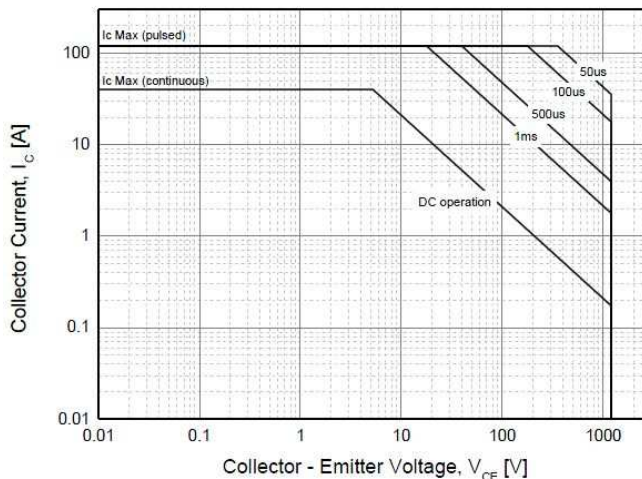


Electrical Characteristics Curve ($T_c = 25^\circ\text{C}$, unless otherwise noted)

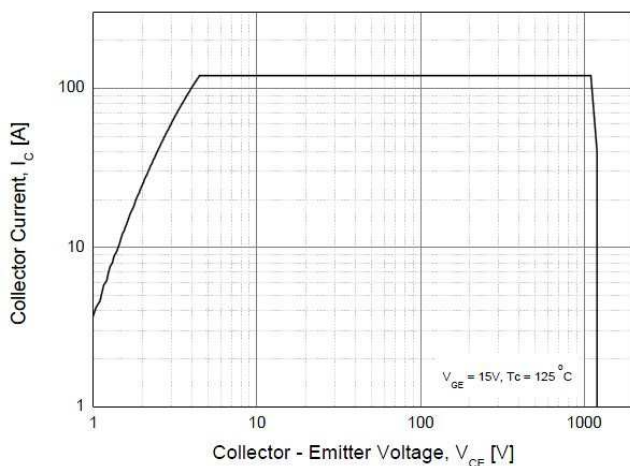
Gate charge characteristics



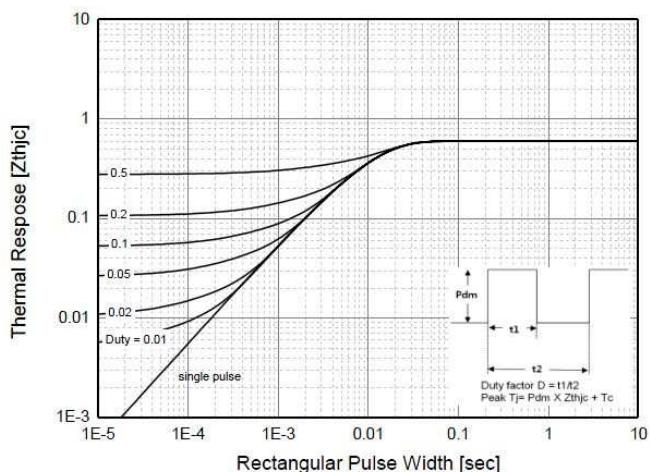
SOA Characteristics



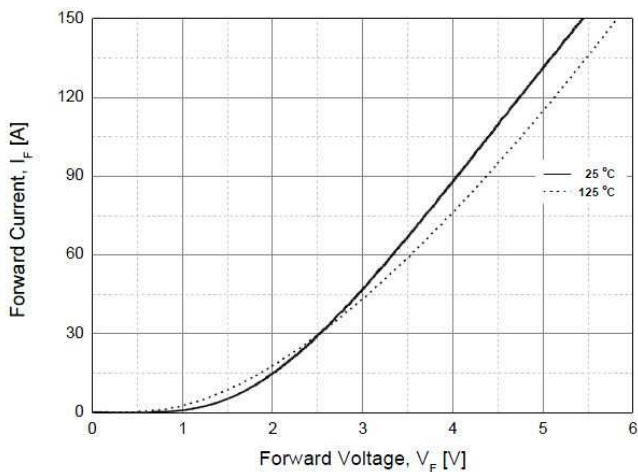
RBSOA



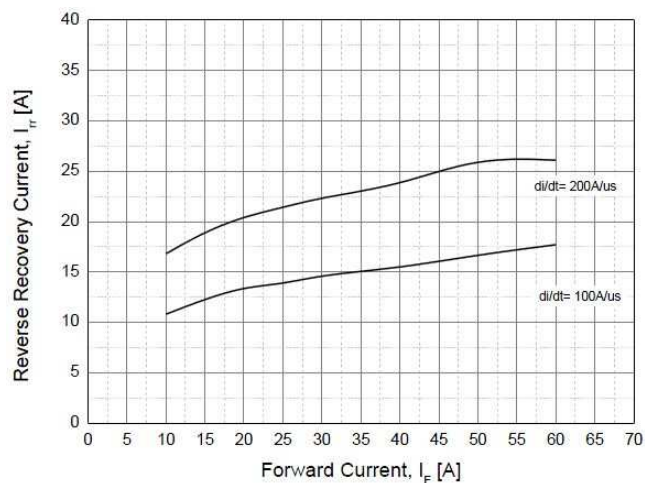
Conduction characteristics



Conduction Characteristics

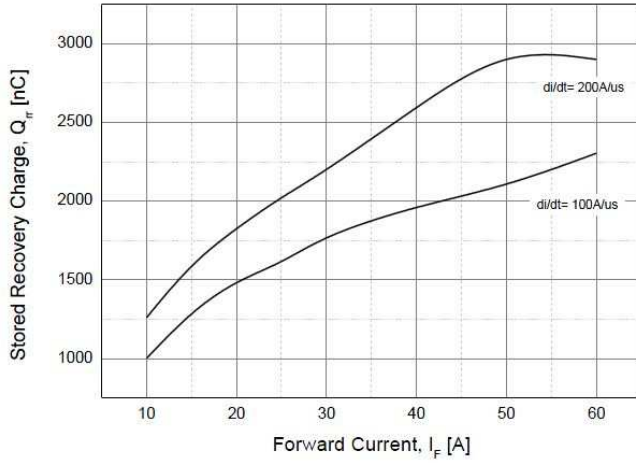


Reverse recovery current vs. forward current

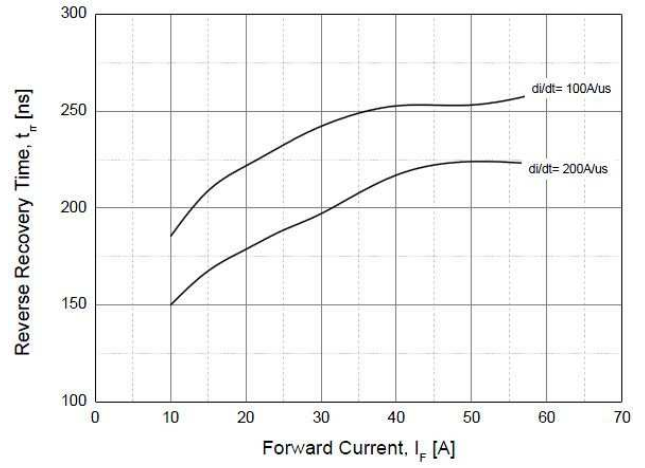


Electrical Characteristics Curve (Tc = 25°C, unless otherwise noted)

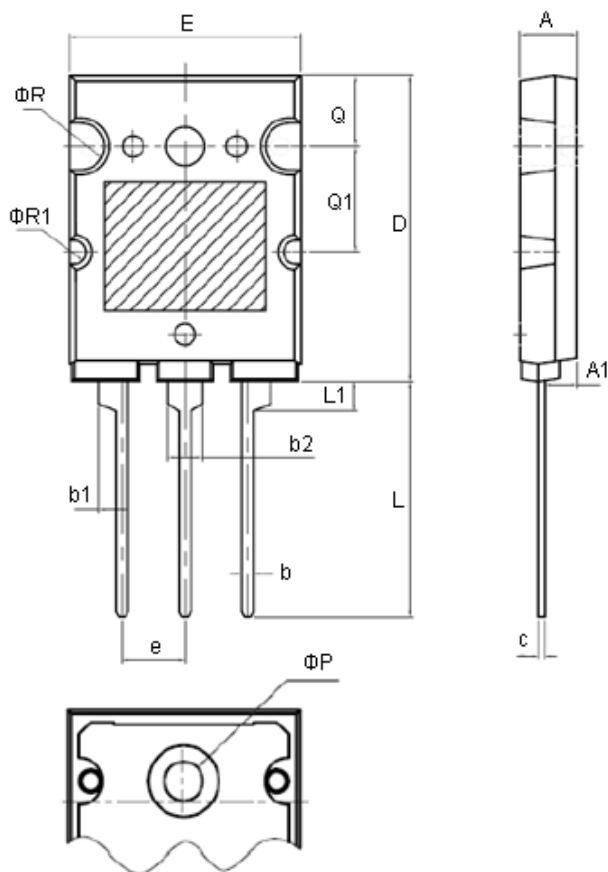
Stored recovery charge vs. forward current



Reverse recovery current vs. forward current



TO-264 Mechanical Drawing



TO-264 DIMENSION						
DIM	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	4.8	5.0	5.2	0.189	0.197	0.205
A1	2.5	2.8	3.1	0.098	0.110	0.122
b	0.90	1.00	1.25	0.035	0.039	0.049
b1	2.3	2.5	2.7	0.091	0.098	0.106
b2	2.8	3.0	3.2	0.110	0.118	0.126
c	0.50	0.60	0.85	0.020	0.024	0.033
D	25.58	26.09	26.59	1.007	1.027	1.047
E	19.30	19.81	20.29	0.760	0.780	0.799
e	5.15	5.45	5.75	0.203	0.215	0.226
L	19.5	20.0	20.5	0.768	0.787	0.807
L1	2.4	2.5	2.6	0.094	0.098	0.102
ΦP	3.10	3.30	3.51	0.122	0.130	0.138
Q	5.8	6.0	6.2	0.228	0.236	0.244
Q1	8.8	9.0	9.2	0.346	0.354	0.362
ΦR	--	2.0	--	--	0.079	--
$\Phi R1$	--	1.0	--	--	0.039	--

TSG40N120CE

N-Channel IGBT with FRD.

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